

L Number	Hits	Search Text	DB	Time stamp
1	4	((("5965301") or ("6335129")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/25 19:10
-	299	(216/87).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:27
-	98	(216/94).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:18
-	546	(216/97).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:19
-	832	(216/99).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:19
-	676	(438/700).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:20
-	570	(438/705).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:20
-	86	(438/746).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:20
-	1065	(216/41).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:25
-	54	levenson adj mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:40
-	29	((216/87).CCLS.) and (Ga or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:39
-	243	((216/94).CCLS.) or ((216/97).CCLS.) or ((216/99).CCLS.) or ((438/700).CCLS.) or ((438/705).CCLS.) or ((438/746).CCLS.) or ((216/41).CCLS.) and (Ga or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:28
-	37	((216/94).CCLS.) or ((216/97).CCLS.) or ((216/99).CCLS.) or ((438/700).CCLS.) or ((438/705).CCLS.) or ((438/746).CCLS.) or ((216/41).CCLS.) and ((Ga or gallium) with ion\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:28
-	21	((216/87).CCLS.) and (Ga or gallium) and ion\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/21 16:29

-	5	(levenson adj mask\$3) and (Ga or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 17:16
-	403	(etch\$3 and (ion\$1 or ion-beam) and (Ga or gallium)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/21 16:45
-	670	etch\$3 same ((ion\$1 or ion-beam) with (Ga or gallium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/21 16:47
-	322	((Ga or Gallium) adj ions) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 13:44
-	27	((Ga or Gallium) adj ions) and etch\$3).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 13:46
-	129	((Ga or Gallium) adj ions) same etch\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:03
-	116	((Ga or Gallium) adj ions) and etch\$3 and (glass or silica\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:13
-	10	((Ga or Gallium) adj ions) and etch\$3 and (glass or silica\$2) and levenson	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:16
-	20	((Ga or Gallium) same ion\$1) and etch\$3 and (glass or silica\$2) and levenson	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:33
-	28	((Ga or Gallium) same ion\$1) and etch\$3 and (glass or silica\$2 or quartz) and levenson	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 17:14
-	134	((Ga or Gallium) same ion\$1) and etch\$3 and (glass or silica\$2 or quartz) and nitric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:52
-	76	((Ga or Gallium) same ion\$1) and etch\$3 and (glass or silica\$2 or quartz) and (sodium adj hydroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 19:10
-	2	((Ga or Gallium) same ion\$1) same etch\$3 same (glass or silica\$2 or quartz) same (sodium adj hydroxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 16:03
-	1	((Ga or Gallium) same ion\$1) and etch\$3 and (glass or silica\$2 or quartz) and (sodium adj hydroxide)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 14:54

-	155	(levenson) and (Ga or gallium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/25 17:16
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